# **JFET VHF/UHF Amplifier**

## **N-Channel - Depletion**

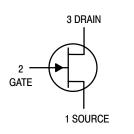
#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	25	Vdc
Drain-Gate Voltage	$V_{DG}$	25	Vdc
Gate-Source Voltage	$V_{GS}$	25	Vdc
Drain Current	I <sub>D</sub>	100	mAdc
Forward Gate Current	$I_{G(f)}$	10	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	350 2.8	mW mW/°C
Storage Channel Temperature Range	T <sub>stg</sub>	-65 to +150	°C



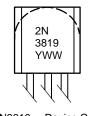
### ON Semiconductor®

#### http://onsemi.com





#### **MARKING DIAGRAM**



2N3819 = Device Code Y = Year WW = Work Week

#### **ORDERING INFORMATION**

Device	Package	Shipping
2N3819	TO-92	5000 Units/Box

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Gate–Source Breakdown Voltage ( $I_G = 1.0 \mu Adc, V_{DS} = 0$ )		V <sub>(BR)GSS</sub>	25	_	_	Vdc
Gate-Source ( $V_{DS} = 15 \text{ Vdc}, I_D = 200 \mu\text{Adc}$ )		V <sub>GS</sub>	0.5	_	7.5	Vdc
Gate-Source Cutoff Voltage (V <sub>DS</sub> = 15 Vdc, I <sub>D</sub> = 10 nAdc)		V <sub>GS(off)</sub>	_	-	-8.0	Vdc
Gate Reverse Current (V <sub>GS</sub> = 15 Vdc, V <sub>DS</sub> = 0)		I <sub>GSS</sub>	_	-	210	nAdc
ON CHARACTERISTICS			•	•	•	•
Zero-Gate-Voltage Drain Curren (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0)	ł	I <sub>DSS</sub>	2.0	_	20	mAdc
SMALL-SIGNAL CHARACTE	RISTICS		•	•	•	•
Forward Transfer Admittance	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ kHz})$	Y <sub>fs</sub>	3.0	_	6.5	mmhos
Output Admittance	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ kHz})$	Y <sub>os</sub>	_	40	_	μmhos
Forward Transfer Admittance	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 200 \text{ MHz})$	Y <sub>fs</sub>	_	5.6	_	mmhos
Reverse Transfer Admittance	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 200 \text{ MHz})$	Y <sub>rs</sub>	_	1.0	_	mmhos
Input Capacitance	$(V_{DS} = 20 \text{ Vdc}, -V_{GS} = 1.0 \text{ Vdc})$	C <sub>iss</sub>	_	3.0	_	pF
Reverse Transfer Capacitance	$(V_{DS} = 20 \text{ Vdc}, -V_{GS} = 1.0 \text{ Vdc}, f = 1.0 \text{ MHz})$	C <sub>rss</sub>	_	0.7	_	pF
Output Capacitance	$(V_{DS} = 20 \text{ Vdc}, -V_{GS} = 1.0 \text{ Vdc}, f = 1.0 \text{ MHz})$	C <sub>oss</sub>	_	0.9	_	pF
Cut-off Frequency (Note 1)	$(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0)$	F <sub>(Yfs)</sub>	_	700	_	MHz

<sup>1.</sup> The frequency at which g<sub>fs</sub> is 0.7 of its value at 1 kHz.

# COMMON SOURCE CHARACTERISTICS ADMITTANCE PARAMETERS

 $(V_{DS} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}C)$ 

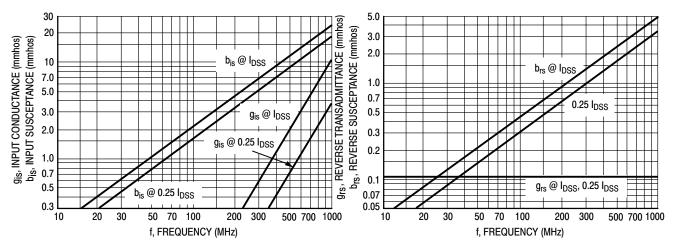


Figure 1. Input Admittance (yis)

Figure 2. Reverse Transfer Admittance (y<sub>rs</sub>)

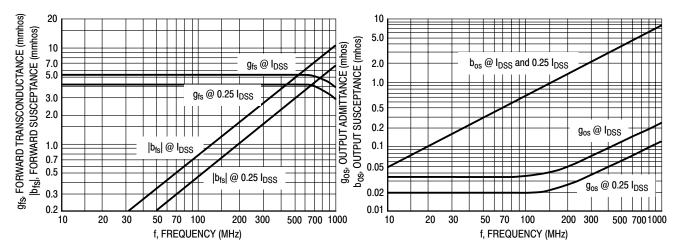
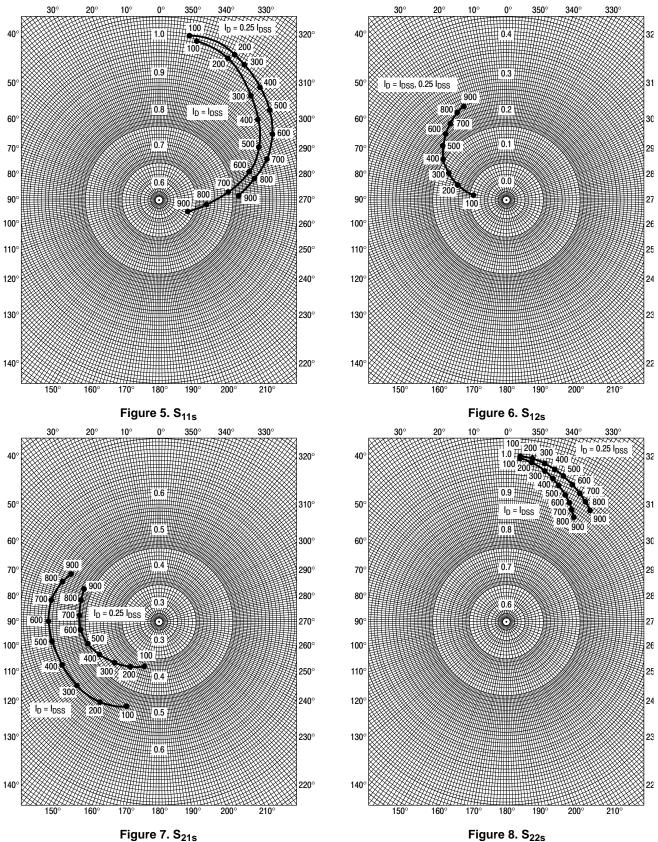


Figure 3. Forward Transadmittance (y<sub>fs</sub>)

Figure 4. Output Admittance (yos)

#### COMMON SOURCE CHARACTERISTICS S-PARAMETERS

 $(V_{DS} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}C, Data Points in MHz)$ 



# COMMON GATE CHARACTERISTICS ADMITTANCE PARAMETERS

 $(V_{DG} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}\text{C})$ 

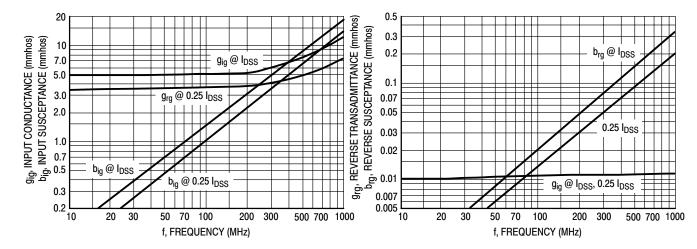


Figure 9. Input Admittance (yiq)

Figure 10. Reverse Transfer Admittance (y<sub>rq</sub>)

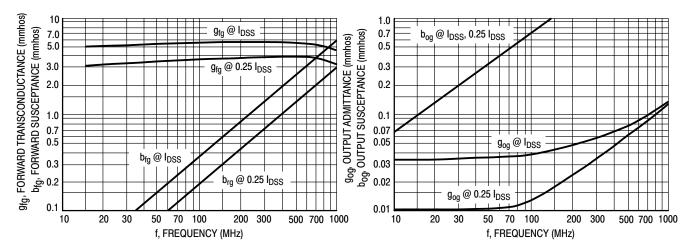
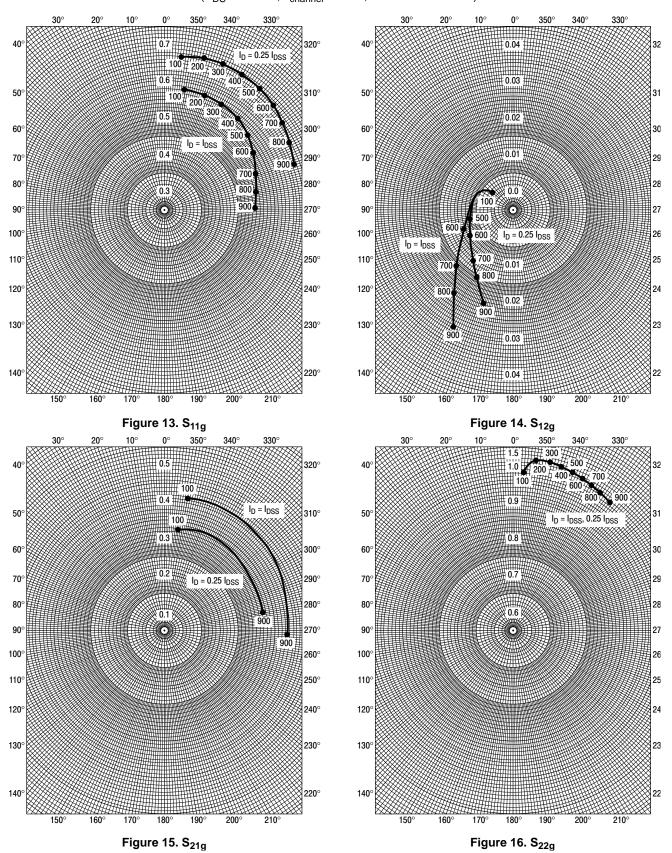


Figure 11. Forward Transfer Admittance (yfg)

Figure 12. Output Admittance (you)

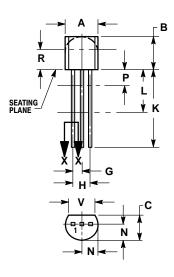
#### COMMON GATE CHARACTERISTICS S-PARAMETERS

 $(V_{DS} = 15 \text{ Vdc}, T_{channel} = 25^{\circ}C, Data Points in MHz)$ 



#### **PACKAGE DIMENSIONS**

## TO-92 (TO-226) CASE 29-11 **ISSUE AL**





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
P		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

- STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN

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